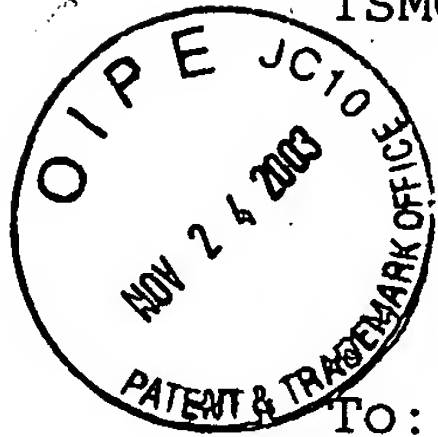


TSMC-01-1629



November 18, 2003

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/647,715 08/25/03

Hornng-Huei Tseng

A MIM CAPACITOR HAVING A HIGH-  
DIELECTRIC-CONSTANT INTERELECTRODE  
INSULATOR AND A METHOD OF FABRICATION

Grp. Art Unit:

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.


The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on November 21, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 11/21/03

U.S. Patent 6,084,765 to Lee, "Integrated Circuit Capacitors Having Recessed Oxidation Barrier Spacers," discusses integrated circuit capacitors utilizing improved spacers to protect diffusion barrier layers from parasitic oxidation and capacitor electrodes from being overetched.

U.S. Patent 5,877,062 to Horii, "Methods of Forming Integrated Circuit Capacitors Having Protected Diffusion Barrier Metal Layers Therein," discloses methods of forming integrated circuit capacitors including the steps of forming an electrically insulating layer having a contact hole therein, on a face of a semiconductor substrate and then forming a polysilicon contact plug in the contact hole.

U.S. Patent 6,232,133 to Kim et al., "Method for Fabricating a Capacitor of Semiconductor Memory Device," provides a method for fabricating a capacitor of semiconductor memory device, which can prevent Ti from diffusing into the ferroelectric layer of capacitor from the Ti adhesive layer.

U.S. Patent 6,277,702 to Chun et al., "Capacitor of a Semiconductor Device and a Method of Fabricating the Same," discloses a storage element of a stacked capacitor having a high dielectric film for a semiconductor device and a method of fabricating the same.

TSMC-01-1629

U.S. Patent 5,994,197 to Liao, "Method for Manufacturing Dynamic Random Access Memory Capable of Increasing the Storage Capacity of the Capacitor," discloses a method for manufacturing the capacitor of a dynamic random access memory cell.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', with a long horizontal stroke extending to the right.

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

Document Number (Optional)

Application Number

TSMC-01-1629

10/647,715

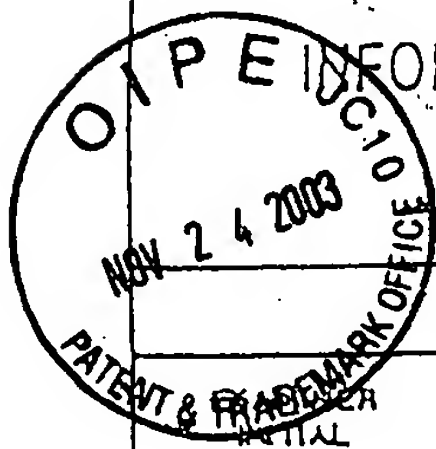
Applicant

Hong-Huei Tseng

Filing Date

08/25/03

Group Art Unit



INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	ALNO DATE IF APPROPRIATE
6084765	7/4/00	Lee	361	311	12/3/98
5877062	3/2/99	Horii	438	396	11/13/97
6232133	5/15/01	Kim et al.	438	3	11/23/99
6277702	8/21/01	Cham et al.	438	396	2/14/00
5994197	11/30/99	Liao	438	396	5/27/99

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.